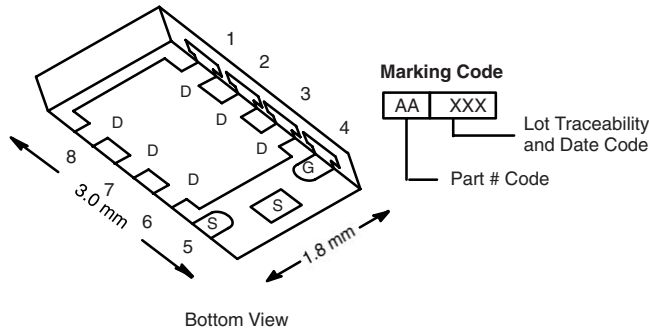


## N-Channel 60-V (D-S) MOSFET

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ.)
60	0.034 at V <sub>GS</sub> = 10 V	12	10.5 nC
	0.041 at V <sub>GS</sub> = 4.5 V	12	

PowerPAK ChipFET Single



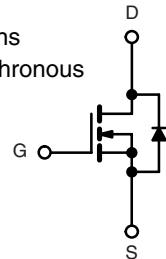
### FEATURES

- Halogen-free
- TrenchFET<sup>®</sup> Power MOSFET
- New Thermally Enhanced PowerPAK<sup>®</sup> ChipFET<sup>®</sup> Package
  - Small Footprint Area
  - Low On-Resistance
  - Thin 0.8 mm Profile



### APPLICATIONS

- Load Switch for Portable Applications
- DC-DC Switch for Low Power Synchronous Rectification
- Intermediate Switch Driver for DC/DC Applications



Ordering Information: Si5476DU-T1-GE3 (Lead (Pb)-free and Halogen-free)

N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T <sub>A</sub> = 25 °C, unless otherwise noted				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V <sub>DS</sub>	60	V	
Gate-Source Voltage	V <sub>GS</sub>	± 20		
Continuous Drain Current (T <sub>J</sub> = 150 °C)	I <sub>D</sub>	T <sub>C</sub> = 25 °C	12 <sup>a</sup>	
		T <sub>C</sub> = 70 °C	12 <sup>a</sup>	
		T <sub>A</sub> = 25 °C	7 <sup>b, c</sup>	
		T <sub>A</sub> = 70 °C	5.6 <sup>b, c</sup>	
Pulsed Drain Current	I <sub>DM</sub>	25	A	
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C		12 <sup>a</sup>
		T <sub>A</sub> = 25 °C		2.6 <sup>b, c</sup>
Avalanche Current	I <sub>AS</sub>	15		mJ
Single Pulse Avalanche Energy	E <sub>AS</sub>	11.2		
Maximum Power Dissipation	P <sub>D</sub>	T <sub>C</sub> = 25 °C	31	
		T <sub>C</sub> = 70 °C	20	
		T <sub>A</sub> = 25 °C	3.1 <sup>b, c</sup>	
		T <sub>A</sub> = 70 °C	2 <sup>b, c</sup>	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C	
Soldering Recommendations (Peak Temperature) <sup>d, e</sup>		260		

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient <sup>b, f</sup>	R <sub>thJA</sub>	34	40	°C/W	
Maximum Junction-to-Case (Drain)	R <sub>thJC</sub>	3	4		

Notes:

- Package limited.
- Surface Mounted on 1" x 1" FR4 board.
- t = 5 s.
- See Solder Profile (<http://www.vishay.com/ppg?73257>). The PowerPAK ChipFET is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.
- Maximum under Steady State conditions is 90 °C/W.



SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	60			V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		55		mV/ $^\circ\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			-6.3		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1		3	V
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			10	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	25			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 4.6\text{ A}$		0.028	0.034	$\Omega$
		$V_{GS} = 4.5\text{ V}, I_D = 4.2\text{ A}$		0.033	0.041	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 4.6\text{ A}$		20		S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		1100		pF
Output Capacitance	$C_{oss}$			90		
Reverse Transfer Capacitance	$C_{rss}$			55		
Total Gate Charge	$Q_g$	$V_{DS} = 30\text{ V}, V_{GS} = 10\text{ V}, I_D = 4.6\text{ A}$		21	32	nC
		$V_{DS} = 30\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 4.6\text{ A}$		10.5	16	
Gate-Source Charge	$Q_{gs}$			3.5		
Gate-Drain Charge	$Q_{gd}$			4.2		
Gate Resistance	$R_g$	$f = 1\text{ MHz}$		3.3		$\Omega$
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 30\text{ V}, R_L = 5.4\text{ }\Omega$ $I_D \cong 5.6\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\text{ }\Omega$		20	30	ns
Rise Time	$t_r$			150	225	
Turn-Off Delay Time	$t_{d(off)}$			20	30	
Fall Time	$t_f$			60	90	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 30\text{ V}, R_L = 5.4\text{ }\Omega$ $I_D \cong 5.6\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		10	15	
Rise Time	$t_r$			15	25	
Turn-Off Delay Time	$t_{d(off)}$			22	40	
Fall Time	$t_f$			10	15	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25\text{ }^\circ\text{C}$			12	A
Pulse Diode Forward Current	$I_{SM}$				25	
Body Diode Voltage	$V_{SD}$	$I_S = 5.5\text{ A}, V_{GS} = 0\text{ V}$		0.85	1.2	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = 5.5\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		25	50	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$			25	50	nC
Reverse Recovery Fall Time	$t_a$			19		ns
Reverse Recovery Rise Time	$t_b$			6		

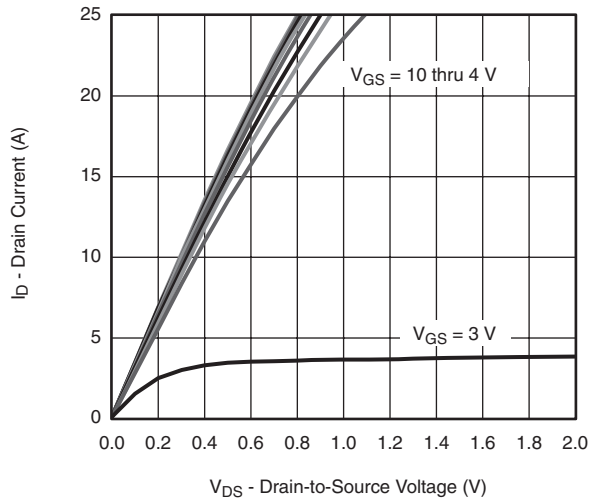
Notes:

- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
b. Guaranteed by design, not subject to production testing.

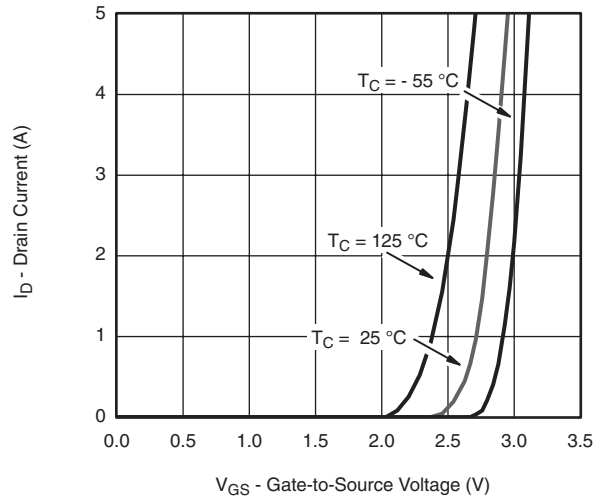
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



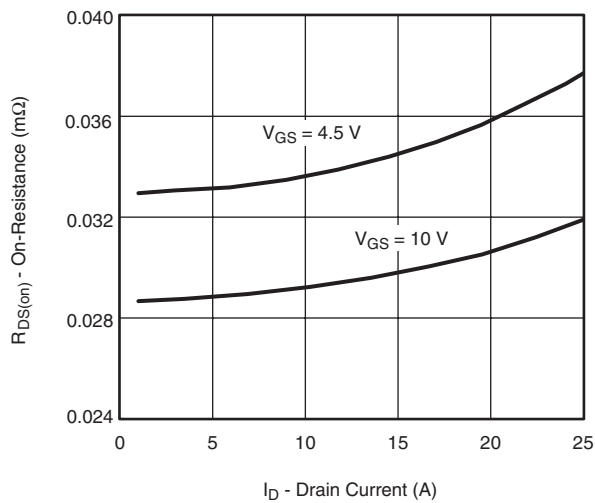
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



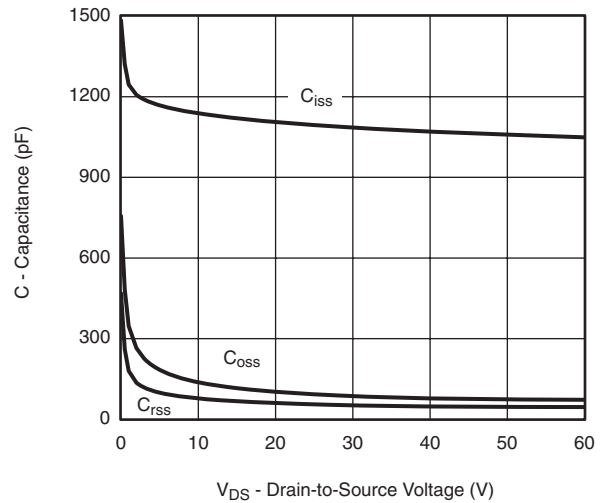
**Output Characteristics**



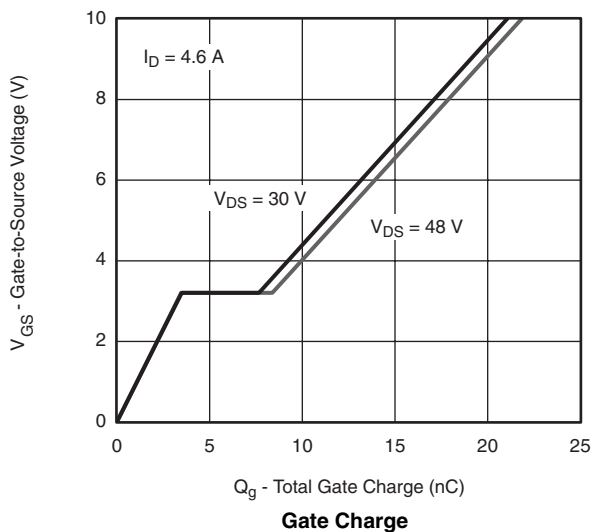
**Transfer Characteristics**



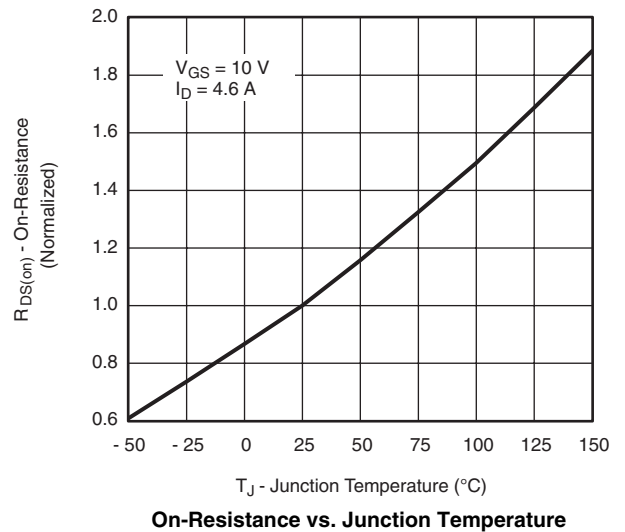
**On-Resistance vs. Drain Current and Gate Voltage**



**Capacitance**



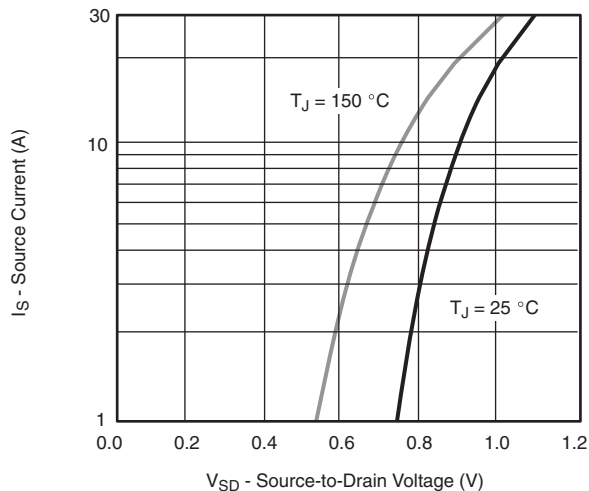
**Gate Charge**



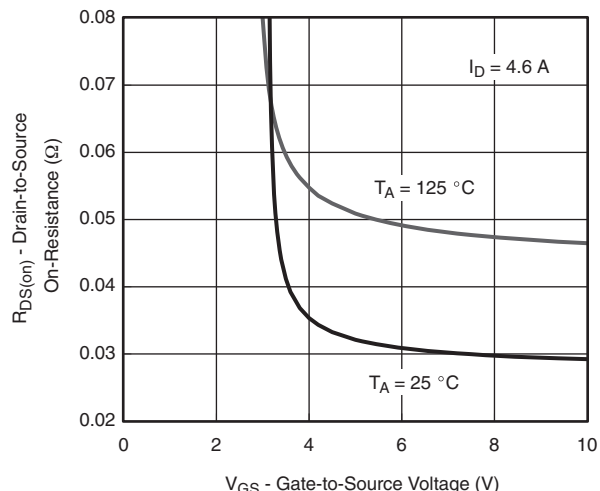
**On-Resistance vs. Junction Temperature**



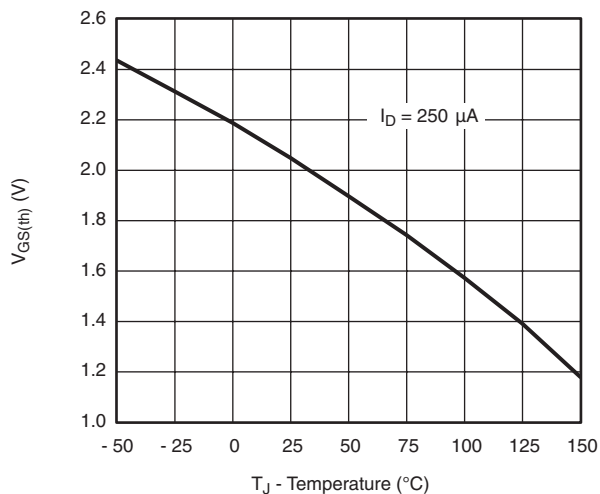
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



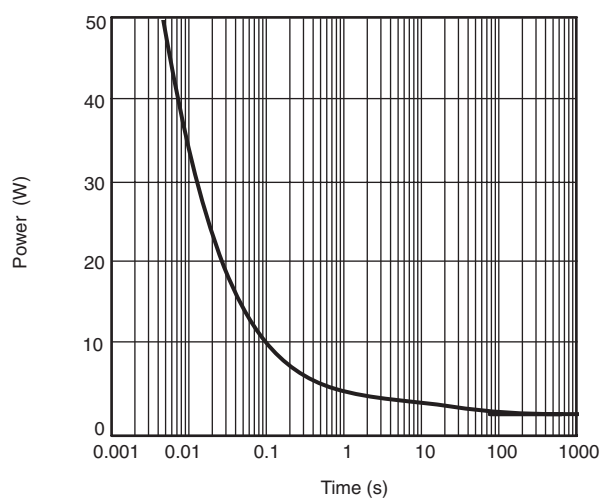
Source-Drain Diode Forward Voltage



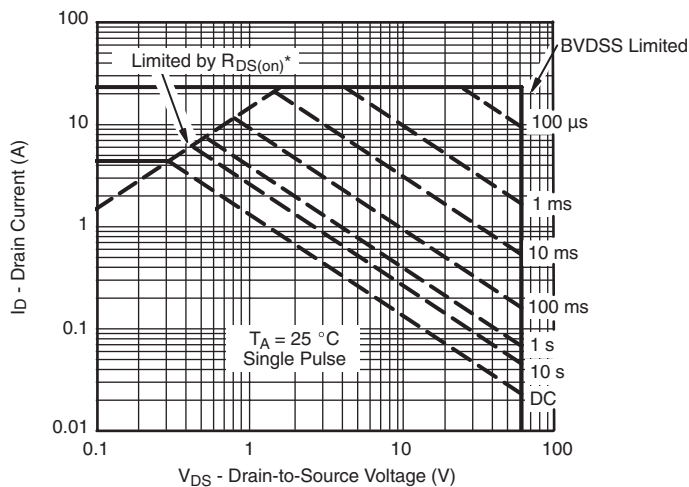
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power, Junction-to-Ambient

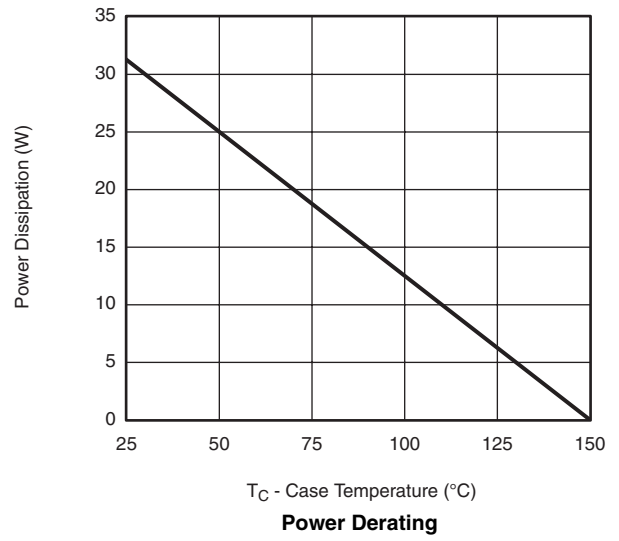
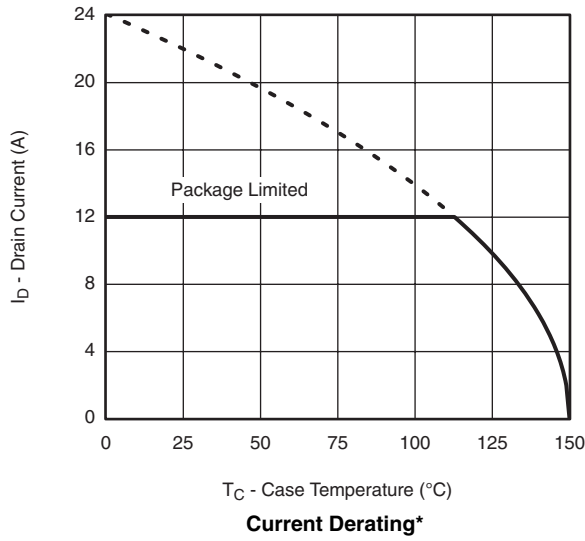


\*  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

Safe Operating Area, Junction-to-Ambient



**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



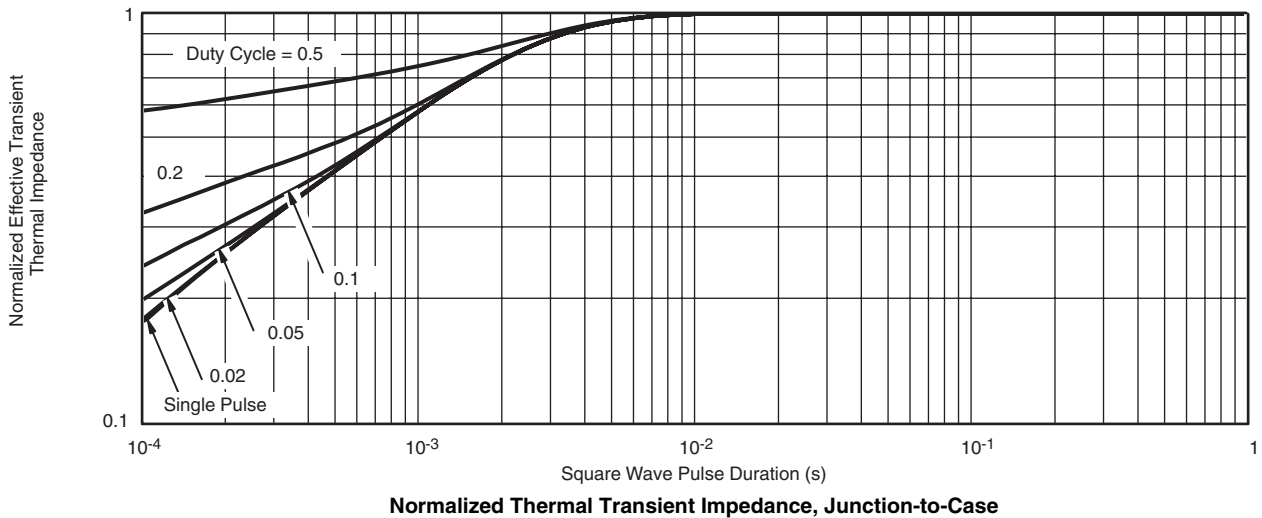
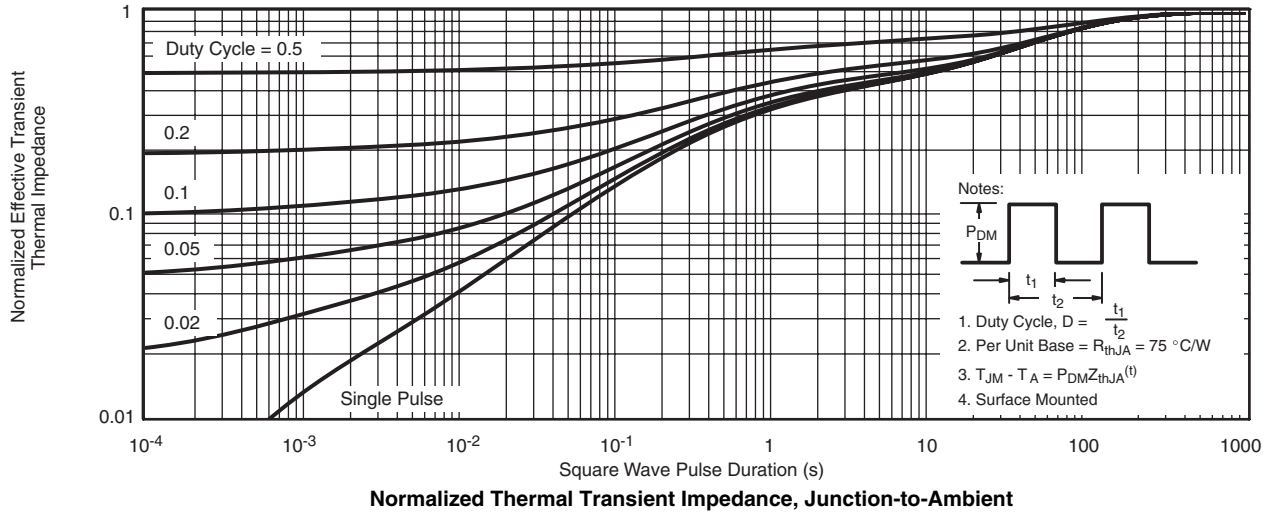
\* The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

# Si5476DU

Vishay Siliconix



**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <http://www.vishay.com/ppg?73663>.

### PowerPAK® ChipFET® Case Outline



DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.70	0.75	0.85	0.028	0.030	0.033
A1	0	-	0.05	0	-	0.002
b	0.25	0.30	0.35	0.010	0.012	0.014
C	0.15	0.20	0.25	0.006	0.008	0.010
D	2.92	3.00	3.08	0.115	0.118	0.121
D1	1.75	1.87	2.00	0.069	0.074	0.079
D2	1.07	1.20	1.32	0.042	0.047	0.052
D3	0.20	0.25	0.30	0.008	0.010	0.012
E	1.82	1.90	1.98	0.072	0.075	0.078
E1	1.38	1.50	1.63	0.054	0.059	0.064
E2	0.92	1.05	1.17	0.036	0.041	0.046
E3	0.45	0.50	0.55	0.018	0.020	0.022
e	0.65 BSC			0.026 BSC		
H	0.15	0.20	0.25	0.006	0.008	0.010
K	0.25	-	-	0.010	-	-
K1	0.30	-	-	0.012	-	-
K2	0.20	-	-	0.008	-	-
K3	0.20	-	-	0.008	-	-
L	0.30	0.35	0.40	0.012	0.014	0.016
C14-0630-Rev. E, 21-Jul-14						
DWG: 5940						

**Note**

- Millimeters will govern

## RECOMMENDED MINIMUM PADS FOR PowerPAK® ChipFET® Single



Recommended Minimum Pads  
Dimensions in mm/(Inches)

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